

2SB1440

Silicon PNP epitaxial planer type

For low-frequency output amplification

Complementary to 2SD2185

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-50	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-3	A
Collector current	I_C	-2	A
Collector power dissipation	P_C	1*	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

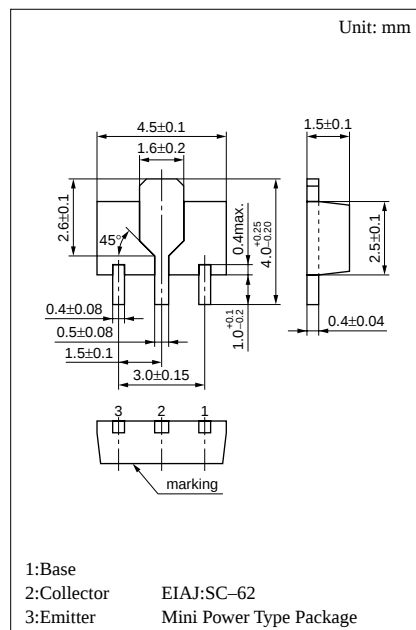
* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25°C)

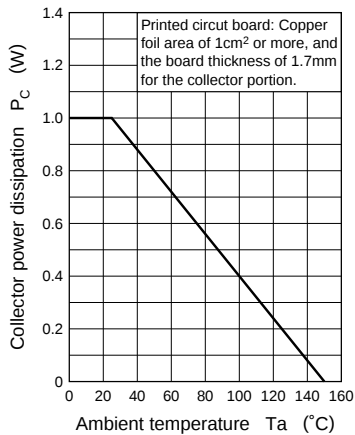
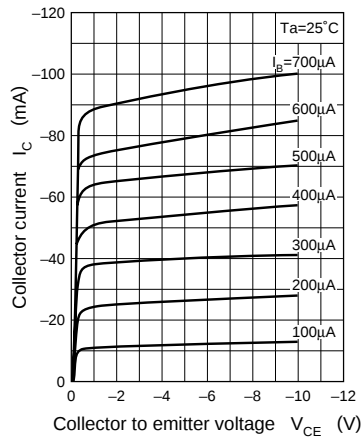
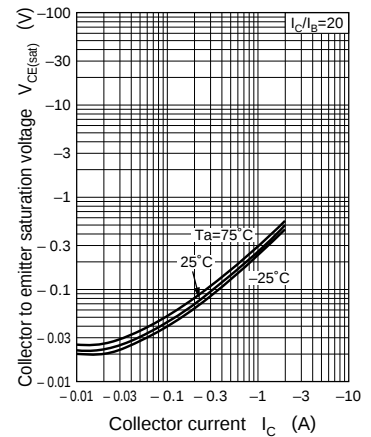
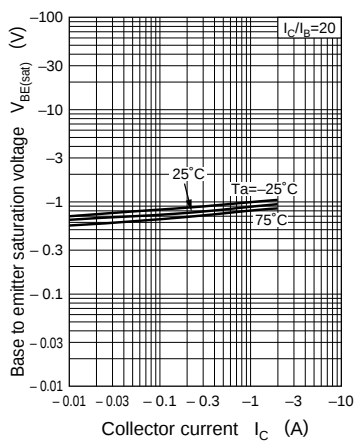
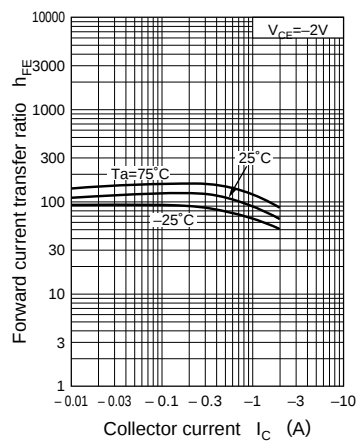
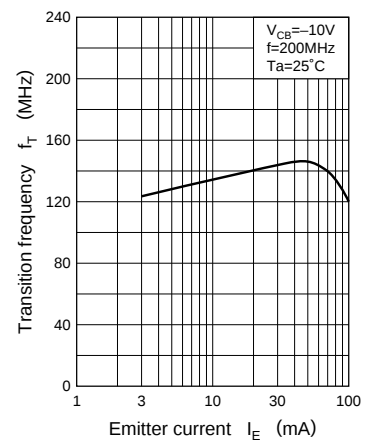
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-50			V
Collector to emitter voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -2V, I_C = -200mA$	120		340	
	h_{FE2}	$V_{CE} = -2V, I_C = -1A$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.2	-0.3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		45	60	pF

* h_{FE1} Rank classification

Rank	R	S
h_{FE1}	120 ~ 240	170 ~ 340



Marking symbol : 11

$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 